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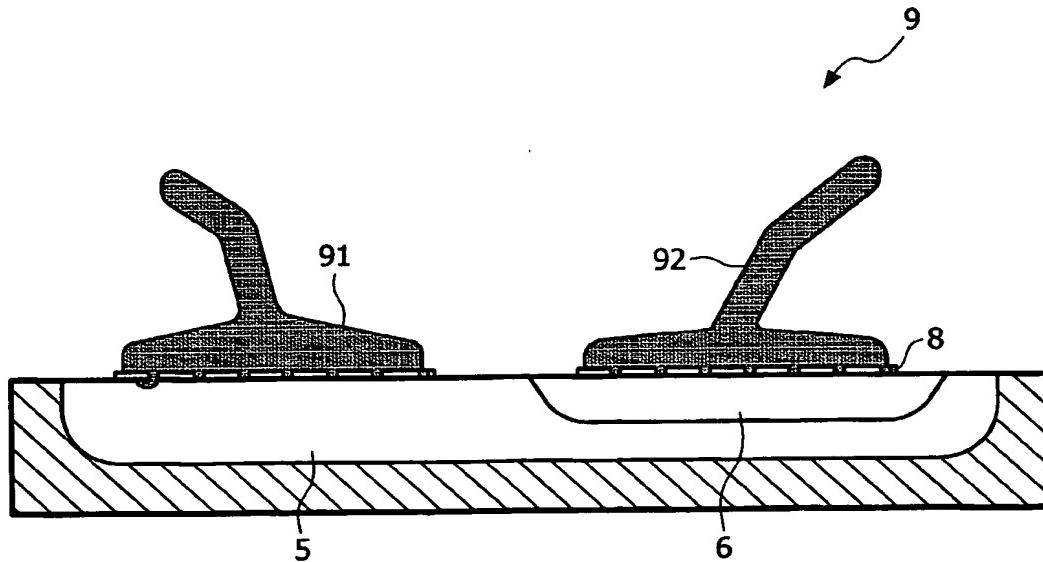
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(54) Title: WIRE-BONDED SEMICONDUCTOR COMPONENT WITH REINFORCED INNER CONNECTION METALLIZATION



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(57) Abstract: A semiconductor component comprising a semiconductor chip 2 made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization 7 in a contact window, and said inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection 9, characterized in that the inner connection metallization comprises a reinforcing system 8 having an open grid structure on the doped silicon substrate.



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